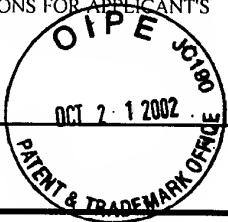
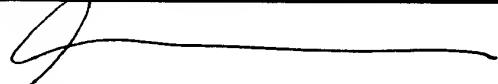
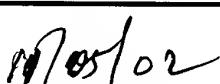


FORM PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT				ATTY. DOCKET NO.		SERIAL NO.:	
				YOR919990123US2		09/936,320	
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				September 12, 2001		2811	
REFERENCE DESIGNATION				U.S. PATENT DOCUMENTS			
EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
<i>JR</i>	AA	5,019,882	05/28/1991	Solomon et al.	357	23.8	May 15, 1989
<i>JR</i>	AB	5,534,713	07/09/1996	Ismail et al.	257	24	May 20, 1994
<i>JR</i>	AC	5,241,197	08/31/1993	Murakami et al.	257	192	September 13, 1991
<i>JR</i>	AD	5,298,452	03/29/1994	Meyerson	437	81	February 21, 1992
<i>JR</i>	AE	5,659,187	08/19/1997	Legoues et al.	257	190	June 7, 1995
<i>JR</i>	AF	5,241,197	08/31/1993	Murakami et al.	257	192	September 13, 1991
<i>JR</i>	AG	5,259,918	11/09/1993	Akbar et al.	156	610	June 12, 1991
	AH						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO
<i>JR</i>	AJ	05 121450 A	15/05/1993	Japan	H01L	21/338	
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>JR</i>	AM	R. People and J.C. Bean, "Band Alignments Of Coherently Strained Ge _x Si _{1-x} / Si Heterostructures On <001> Ge _y Si _{1-y} Substrates"; Appl. Phys. Lett. 48 (8); pp. 538-539; February 24, 1986.					
<i>JR</i>	AN	G. Hock et al., "High Performance 0.25μm p-Type Ge/SiGe MODFETs"; Electronics Letters; Vol. 34; No. 19; pp. 1888-1889; September 17, 1998.					
<i>JR</i>	AO	U. Konig and F. Schaffler, "p-Type Ge-Channel MODFET's With High Transconductance Grown On Si Substrates"; IEEE Electron Device Letters; Vol. 14; No. 4; pp. 205-207; April 1993.					
EXAMINER 				DATE CONSIDERED 			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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		OCT 2 1 2002 PATENT & TRADEMARK OFFICE				
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REFERENCE DESIGNATION U.S. PATENT DOCUMENTS						
EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
BA						
BB						
BC						
FOREIGN PATENT DOCUMENTS						
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
						YES NO
BD						
BE						
BF						
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)						
<i>R</i>	BE	M. Arafa, "A 70-GHz f_T Low Operating Bias Self-Aligned p-Type SiGe MODFET"; IEEE Electron Device Letters; Vol. 17; No. 12; pp. 586-588; December 1996.				
<i>R</i>	BF	U. Kong et al., "SiGe HBTs And HFETs"; IEEE Solid State Electronics; Vol. 38; No. 9; pp. 1595-1602; Elsevier; 1995.				
<i>R</i>	BG	Milind Gokhale et al., "Enhanced Performance Of PMOS and CMOS Circuits Using Self-Aligned MOSFETs With Modulation Doped Si-Ge Channel"; Proceedings of the Tenth Biennial University/ Government/Industry Microelectronics Symposium; 1993 IEEE; US; New York; pp.219-222; May 18-19, 1993.				
<i>R</i>	BH	David W. Greve, "Field Effect Devices And Applications"; Prentice-Hall, Inc; Simon & Schuster/ A Viacom Company; Upper Saddle River, NJ, 07458; Chap. 8: Structure Of The GaAs MESFET; p.315; Table 8.1; 1998.				
EXAMINER <i>[Signature]</i>			DATE CONSIDERED <i>11/05/02</i>			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance <u>and</u> not considered. Include copy of this form with next communication to applicant.						